# **ON Semiconductor**

# Is Now



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# Silicon Carbide Schottky Diode

# 1200 V, 20 A

# **Description**

Silicon Carbide (SiC) Schottky Diodes use a completely new technology that provides superior switching performance and higher reliability compared to Silicon. No reverse recovery current, temperature independent switching characteristics, and excellent thermal performance sets Silicon Carbide as the next generation of power semiconductor. System benefits include highest efficiency, faster operating frequency, increased power density, reduced EMI, and reduced system size & cost.

#### **Features**

- Max Junction Temperature 175°C
- Avalanche Rated 200 mJ
- High Surge Current Capacity
- Positive Temperature Coefficient
- Ease of Paralleling
- No Reverse Recovery / No Forward Recovery
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

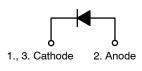
# **Applications**

- General Purpose
- SMPS, Solar Inverter, UPS
- Power Switching Circuits



# ON Semiconductor®

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**Schottky Diode** 



D<sup>2</sup>PAK-3 (TO-263, 3-LEAD) CASE 418AJ

#### **MARKING DIAGRAM**



\$Y = ON Semiconductor Logo &Z = Assembly Plant Code

&3 = Numeric Date Code

&K = Lot Code FFSB20120A = Specific Device Code

### **ORDERING INFORMATION**

See detailed ordering and shipping information on page 2 of this data sheet.

# **ABSOLUTE MAXIMUM RATINGS** ( $T_C = 25^{\circ}C$ unless otherwise noted)

Symbol	Parameter		Value	Unit
$V_{RRM}$	Peak Repetitive Reverse Voltage	ak Repetitive Reverse Voltage		V
E <sub>AS</sub>	Single Pulse Avalanche Energy (Note 1)		200	mJ
IF	Continuous Rectified Forward Current @ T <sub>C</sub> < 157°C		20	Α
	Continuous Rectified Forward Current @ T <sub>C</sub> <	orward Current @ T <sub>C</sub> < 135°C		
I <sub>F, Max</sub>	Non-Repetitive Peak Forward Surge Current	T <sub>C</sub> = 25°C, 10 μs	1190	Α
		T <sub>C</sub> = 150°C, 10 μs	990	Α
I <sub>F,SM</sub>	Non-Repetitive Forward Surge Current	Half-Sine Pulse, t <sub>p</sub> = 8.3 ms	135	Α
I <sub>F,RM</sub>	Repetitive Forward Surge Current	Half-Sine Pulse, t <sub>p</sub> = 8.3 ms	74	Α
Ptot	Power Dissipation	T <sub>C</sub> = 25°C	333	W
		T <sub>C</sub> = 150°C	55	W
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range	•	-55 to +175	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

# THERMAL CHARACTERISTICS

Symbol	Parameter	Value	Unit
$R_{ heta JC}$	Thermal Resistance, Junction to Case, Max	0.45	°C/W

# **ELECTRICAL CHARACTERISTICS** (T<sub>C</sub> = 25°C unless otherwise noted)

Symbol	Parameter	Test Condition	Min	Тур	Max	Unit
V <sub>F</sub>	Forward Voltage	I <sub>F</sub> = 20 A, T <sub>C</sub> = 25°C	-	1.45	1.75	V
		I <sub>F</sub> = 20 A, T <sub>C</sub> = 125°C	=	1.7	2.0	
		I <sub>F</sub> = 20 A, T <sub>C</sub> = 175°C	=	2.0	2.4	
I <sub>R</sub>	Reverse Current	V <sub>R</sub> = 1200 V, T <sub>C</sub> = 25°C	=	=	200	μΑ
		V <sub>R</sub> = 1200 V, T <sub>C</sub> = 125°C	=	=	300	
		V <sub>R</sub> = 1200 V, T <sub>C</sub> = 175°C	=	=	400	
$Q_C$	Total Capacitive Charge	V = 800 V	-	120	-	nC
С	Total Capacitance	V <sub>R</sub> = 1 V, f = 100 kHz	-	1220	-	pF
		V <sub>R</sub> = 400 V, f = 100 kHz	-	111	-	
		V <sub>R</sub> = 800 V, f = 100 kHz	_	88	_	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

# **ORDERING INFORMATION**

Part Number	Top Marking	Package	Shipping
FFSB20120A	FFSB20120A	D <sup>2</sup> PAK–3 (Pb-Free / Halogen Free)	800 / Tape & Reel

<sup>1.</sup>  $E_{AS}$  of 200 mJ is based on starting  $T_J = 25^{\circ}C$ , L = 0.5 mH,  $I_{AS} = 29$  A, V = 50 V.

# **TYPICAL CHARACTERISTICS**

 $(T_J = 25^{\circ}C \text{ unless otherwise noted})$ 

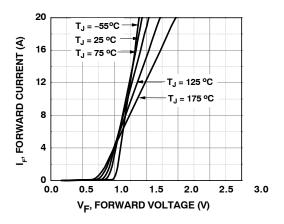


Figure 1. Forward Characteristics

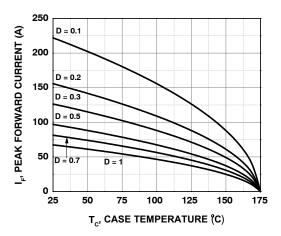


Figure 3. Current Derating

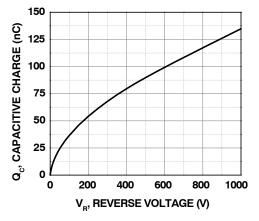


Figure 5. Capacitive Charge vs. Reverse Voltage

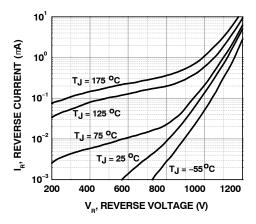


Figure 2. Reverse Characteristics

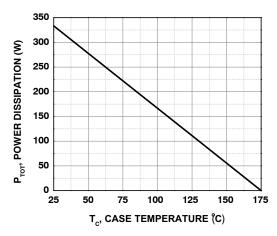


Figure 4. Power Derating

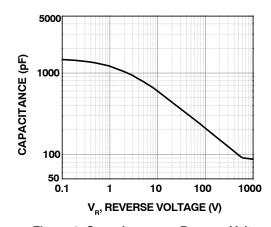


Figure 6. Capacitance vs. Reverse Voltage

# **TYPICAL CHARACTERISTICS**

 $(T_J = 25^{\circ}C \text{ unless otherwise noted})$ 

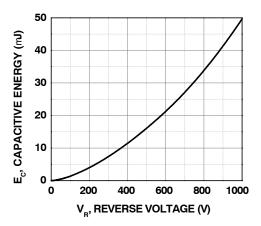


Figure 7. Capacitance Stored Energy

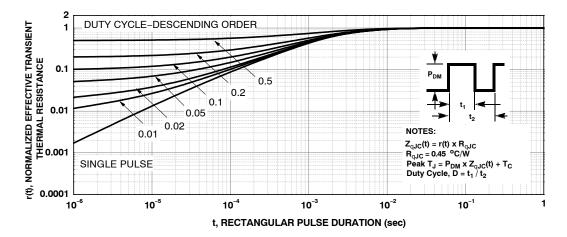


Figure 8. Junction-to-Case Transient Thermal Response Curve

# **TEST CIRCUIT AND WAVEFORMS**

L = 0.5 mH R < 0.1  $\Omega$   $V_{DD}$  = 50 V EAVL = 1/2L12 [ $V_{R(AVL)}$  / ( $V_{R(AVL)}$  –  $V_{DD}$ )] Q1 = IGBT (BV<sub>CES</sub> > DUT V<sub>R(AVL)</sub>)

SENSE

DUT

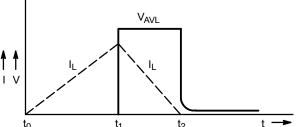
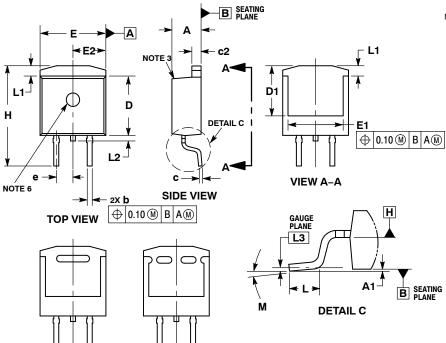


Figure 9. Unclamped Inductive Switching Test Circuit & Waveform

 $V_{DD} \\$ 

#### **PACKAGE DIMENSIONS**

### D<sup>2</sup>PAK-3 (TO-263, 3-LEAD) CASE 418AJ **ISSUE B**



VIEW A-A
OPTIONAL CONSTRUCTIONS

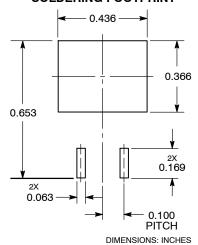
#### NOTES:

- NOTES:

  1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
  2. CONTROLLING DIMENSION: INCHES.
  3. CHAMFER OPTIONAL
  4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.005 PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY AT DATUM H.
  5. THERMAL PAD CONTOUR IS OPTIONAL WITHIN DIMENSIONS E, L1, D1 AND E1.
  6. OPTIONAL MOLD FEATURE

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
Α	0.160	0.190	4.06	4.83
<b>A</b> 1	0.000	0.010	0.00	0.25
q	0.020	0.039	0.51	0.99
С	0.012	0.029	0.30	0.74
c2	0.045	0.065	1.14	1.65
D	0.330	0.380	8.38	9.65
D1	0.260		6.60	
Е	0.380	0.420	9.65	10.67
E1	0.245		6.22	
е	0.100 BSC		2.54 BSC	
Н	0.575	0.625	14.60	15.88
L	0.070	0.110	1.78	2.79
L1		0.066		1.68
L2		0.070		1.78
L3	0.010	BSC	0.25 BSC	
М	0°	8°	0°	8°

#### **RECOMMENDED SOLDERING FOOTPRINT\***



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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SS3003CH-TL-E GA01SHT18 CRS10I30A(TE85L,QM MA4E2501L-1290 MBRB30H30CT-1G SB007-03C-TB-E SK32A-TP SK33B-TP
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ACDBA140-HF ACDBA2100-HF ACDBA3100-HF CDBQC0530L-HF ACDBA340-HF ACDBA260LR-HF ACDBA1100-HF SK310B-TP
MA4E2502L-1246 MA4E2502H-1246 NRVBM120ET1G NSR01L30MXT5G NTE573 NTE6081 SB560 PMAD1108-LF SD103ATW-TP